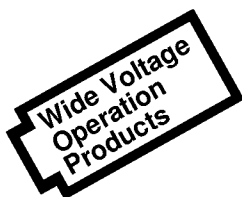


SRM2B256SLMX_{55/70/10}

256K-Bit Static RAM



- Wide Temperature Range
- Extremely Low Standby Current
- Access Time 100ns (2.7V) /55ns (4.5V)
- 32,768 Words×8-bit Asynchronous

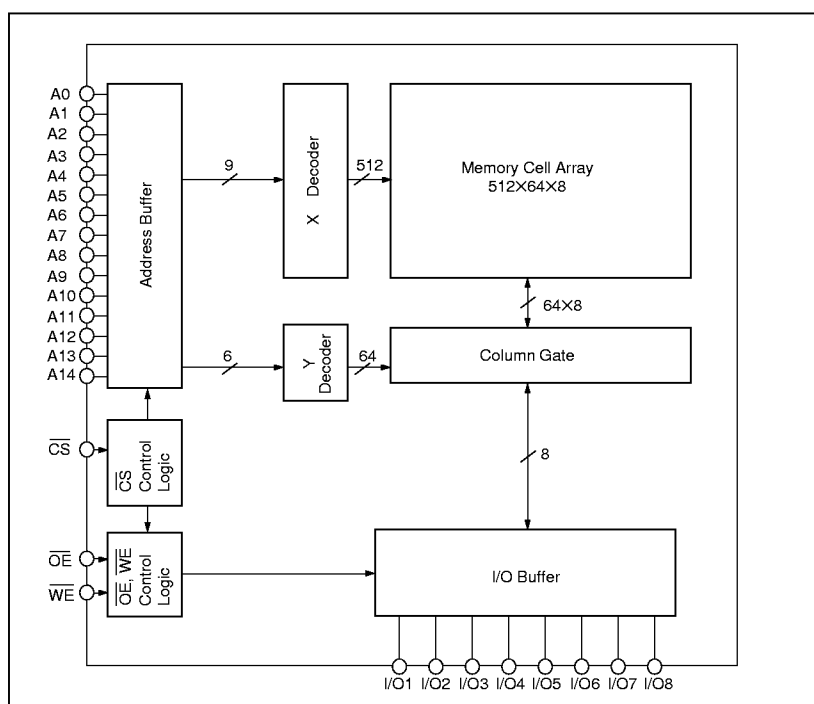
DESCRIPTION

The SRM2B256SLMX is a low voltage operating 32,768 words×8-bit asynchronous, static, random access memory fabricated using an advanced CMOS technology. Its very low standby power consumption makes it ideal for applications requiring non-volatile storage with back-up batteries. And -25 to 85°C operating temperature range makes it ideal for industrial use. The asynchronous and static nature of the memory requires no external clock or refresh circuit. Output ports are 3-state output allows easy expansion of memory capacity. These features makes the SRM2B256SLMX usable for wide range of applications from microprocessor systems to terminal devices.

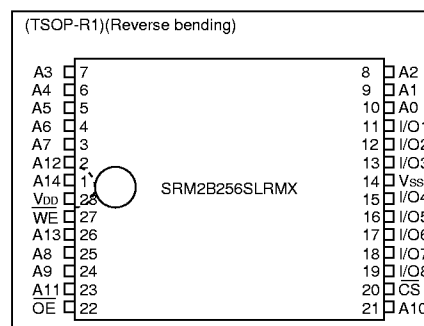
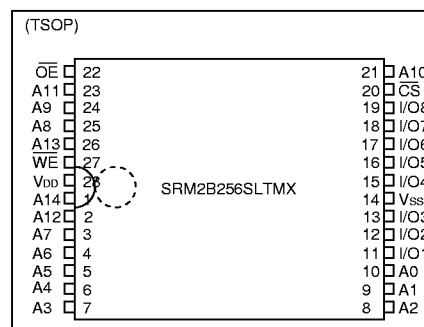
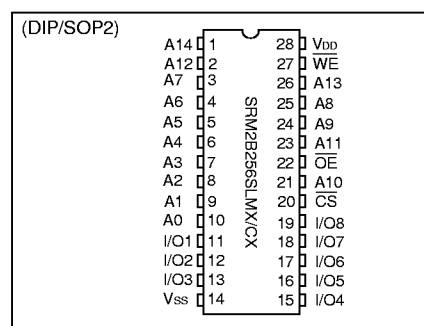
FEATURES

- Wide temperature range -25 to 85°C
- Extended supply voltage range 2.7 to 5.5V
- Fast access time 100ns (3V±10%)
55ns (5V±10%)
- Extremely low standby current SL Version
- Completely static no clock required
- 3-state output
- Battery back-up operation
- Package SRM2B256SLCX DIP2-28pin (plastic)
SRM2B256SLMX SOP2-28pin (plastic)
SRM2B256SLTMX TSOP (I)-28pin (plastic)
SRM2B256SLRMX TSOP (I)-28pin-R1 (plastic)

BLOCK DIAGRAM



PIN CONFIGURATION



PIN DESCRIPTION

A0 to A14	Address Input
WE	Write Enable
OE	Output Enable
CS	Chip Select
I/O1 to I/O8	Data Input/Output
VDD	Power Supply (2.7 to 5.5V)
VSS	Power Supply (0V)

■ ABSOLUTE MAXIMUM RATINGS

(V_{SS}=0V)

Parameter	Symbol	Rating	Unit
Supply voltage	V _{DD}	-0.5 to 7.0	V
Input voltage	V _I	-0.5* to 7.0	V
Input/Output voltage	V _{I/O}	-0.5* to V _{DD} +0.3	V
Power dissipation	P _D	1.0	W
Operating temperature	T _{opr}	-25 to 85	°C
Storage temperature	T _{stg}	-65 to 150	°C
Soldering temperature and time	T _{sol}	260°C, 10s (Lead only)	—

*V_I, V_{I/O}(Min.) = -3.0V when pulse width is less or equal to 50ns

■ DC RECOMMENDED OPERATING CONDITIONS

(V_{SS}=0V, Ta=-25 to 85°C)

Parameter	Symbol	V _{DD} =3V±10%			V _{DD} =5V±10%			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
Supply voltage	V _{DD}	2.7	—	3.3	4.5	—	5.5	V
	V _{SS}	0	—	0	0	—	0	V
Input voltage	V _{IH}	2.2	—	V _{DD} +0.3	2.2	—	V _{DD} +0.3	V
	V _{IL}	-0.3*	—	0.4	-0.3*	—	0.8	V

*V_{IL} (Min.) = -3V when pulse width is less or equal to 50ns

■ ELECTRICAL CHARACTERISTICS

● DC Electrical Characteristics

(V_{SS}=0V, Ta=-25 to 85°C)

Parameter	Symbol	Conditions	V _{DD} =3V±10%			V _{DD} =5V±10%			Unit
			Min.	Typ.*1	Max.	Min.	Typ.*2	Max.	
Input leakage	I _{LI}	V _I =0 to V _{DD}	-1.0	—	1.0	-1.0	—	1.0	μA
Standby supply current	I _{DDS}	$\overline{CS}=V_{IH}$	—	—	2	—	—	3.0	mA
	I _{DDS1}	$\overline{CS} \geq V_{DD}-0.2V$	—	0.3	25	—	0.5	50	μA
Average operating current	I _{DDA}	V _I =V _{IL} , V _{IH} I _{I/O} =0mA, t _{cyc} =Min.	—	10	15	—	30	45	mA
	I _{DDA1}	V _I =V _{IL} , V _{IH} I _{I/O} =0mA, t _{cyc} =1μs	—	—	5	—	—	10	mA
Operating supply current	I _{DDO}	V _I =V _{IL} , V _{IH} I _{I/O} =0mA	—	—	5	—	—	10	mA
Output leakage	I _{LO}	$\overline{CS}=V_{IH}$ or $\overline{WE}=V_{IL}$ or $\overline{OE}=V_{IH}$, V _{I/O} =0 to V _{DD}	-1.0	—	1.0	-1.0	—	1.0	μA
High level output voltage	V _{OH}	I _{OH} =-1.0mA, -0.5mA*3	2.4	—	—	2.4	—	—	V
Low level output voltage	V _{OL}	I _{OL} =2.1mA, 1.0mA*3	—	—	0.4	—	—	0.4	V

*1 Typical values are measured at Ta=25°C and V_{DD}=3.0V*2 Typical values are measured at Ta=25°C and V_{DD}=5.0V*3 V_{DD}=3V±10%

● Terminal Capacitance

(f=1MHz, Ta=25°C)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Input Capacitance	C _I	V _I =0V	—	—	8	pF
I/O Capacitance	C _{I/O}	V _{I/O} =0V	—	—	10	pF

● AC Electrical Characteristics

○ Read Cycle

(V_{SS}=0V, Ta=-25 to 85°C)

Parameter	Symbol	Conditions	SRM2B256SLMX55				SRM2B256SLMX70				SRM2B256SLMX10				Unit
			V _{DD} =3V±10%		V _{DD} =5V±10%		V _{DD} =3V±10%		V _{DD} =5V±10%		V _{DD} =3V±10%		V _{DD} =5V±10%		
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Read cycle time	t _{RC}	*1	100	—	55	—	120	—	70	—	180	—	100	—	nS
Address access time	t _{ACC}		—	100	—	55	—	120	—	70	—	180	—	100	nS
CS access time	t _{ACS}		—	100	—	55	—	120	—	70	—	180	—	100	nS
OE access time	t _{OE}		—	60	—	30	—	70	—	35	—	90	—	45	nS
CS output set time	t _{CLZ}	*2	15	—	10	—	15	—	10	—	15	—	10	—	nS
CS output floating	t _{CHZ}		—	35	—	20	—	40	—	25	—	50	—	35	nS
OE output set time	t _{OLZ}		5	—	5(0)	—	5	—	5(0)	—	5	—	5(0)	—	nS
OE output floating	t _{OHZ}		—	35	—	20	—	40	—	25	—	50	—	35	nS
Output hold time	t _{OH}	*1	15	—	10	—	15	—	10	—	15	—	10	—	nS

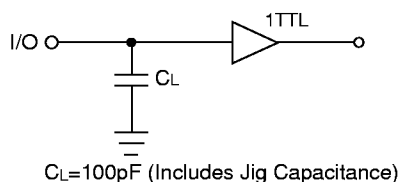
○ Write Cycle

(V_{SS}=0V, Ta=-25 to 85°C)

Parameter	Symbol	Conditions	SRM2B256SLMX55				SRM2B256SLMX70				SRM2B256SLMX10				Unit
			V _{DD} =3V±10%		V _{DD} =5V±10%		V _{DD} =3V±10%		V _{DD} =5V±10%		V _{DD} =3V±10%		V _{DD} =5V±10%		
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Write cycle time	t _{WC}	*1	100	—	55	—	120	—	70	—	180	—	100	—	nS
Chip select time	t _{CW}		80	—	50	—	90	—	60	—	110	—	80	—	nS
Address valid to end of write	t _{AW}		80	—	50	—	90	—	60	—	110	—	80	—	nS
Address setup time	t _{AS}		0	—	0	—	0	—	0	—	0	—	0	—	nS
Write pulse width	t _{WP}		75	—	40	—	80	—	45	—	100	—	60	—	nS
Address hold time	t _{WR}		0	—	0	—	0	—	0	—	0	—	0	—	nS
Input data set time	t _{DW}		40	—	25	—	45	—	30	—	60	—	40	—	nS
Input data hold time	t _{DH}		0	—	0	—	0	—	0	—	0	—	0	—	nS
Write to Output floating	t _{WHZ}	*2	—	35	—	20	—	40	—	25	—	50	—	35	nS
Output Active from end to wirt	t _{OW}		5	—	5	—	5	—	5	—	5	—	5	—	nS

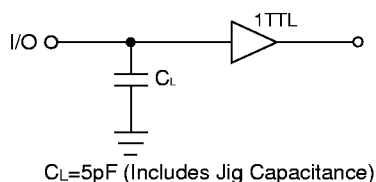
*1 Test Conditions

1. Input pulse level: 0.6V to 2.4V(5V)/0.4V to 2.2V(3V)
2. t_r=t_f=5ns
3. Input and output timing reference levels : 1.5V
4. Output load C_L=100pF



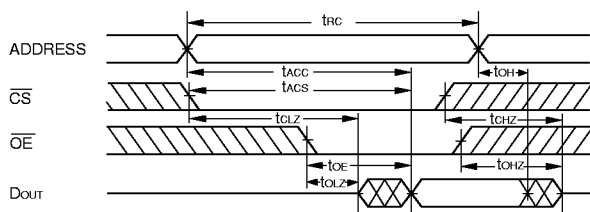
*2 Test Conditions

1. Input pulse level : 0.6V to 2.4V(5V)/0.4V to 2.2V(3V)
2. t_r=t_f=5ns
3. Input timing reference levels: 1.5V
4. Output timing reference levels:
±200mV (the level displaced from stable output voltage level)
5. Output load C_L=5pF

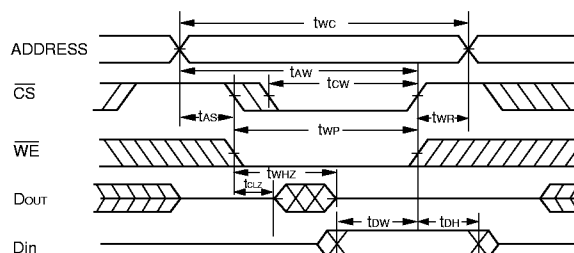


● Timing chart

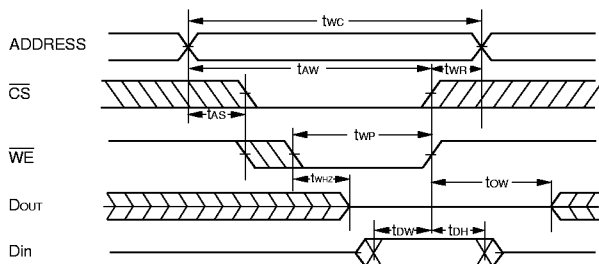
○ Read Cycle*1



○ Write Cycle (1) (CS Control)*2



○ Write Cycle (2) (WE Control)*3



Note :

- *1 During read cycle time, WE is to be "H" level.
- *2 During write cycle time that is controlled by CS, Output Buffer is in high impedance state, whether OE level is "H" or "L".
- *3 During write cycle time that is controlled by WE, Output Buffer is in high impedance state if OE is "H" level.

■ DATA RETENTION CHARACTERISTIC WITH LOW VOLTAGE POWER SUPPLY

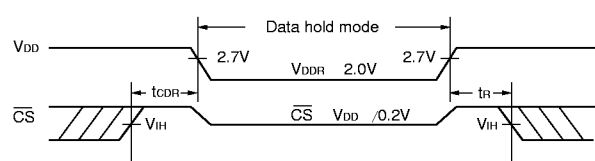
($V_{SS}=0V$, $T_a=-25$ to $85^{\circ}C$)

Parameter	Symbol	Conditions	Min.	Typ.*1	Max.	Unit
Data retention Supply voltage	V_{DDR}		2.0	—	5.5	V
Data retention current	I_{DDR}	$V_{DD}=3V$, $\overline{CS} \geq V_{DD}-0.2V$	—	0.25	20(2*2)	μA
Chip select data hold time	t_{CDR}		0	—	—	ns
Operation recovery time	t_R		5	—	—	ms

*1 Typical values are measured at $25^{\circ}C$

*2 Typical values are measured at $40^{\circ}C$

Data retention timing



Note: During standby mode in which the data is retentive, the supply voltage (V_{DD}) can be in low voltage until $V_{DD}=V_{DDR}$.

At this mode data reading and writing are impossible.

■ FUNCTIONS

● Truth Table

$\overline{CS}$	$\overline{OE}$	$\overline{WE}$	A0 to A14	DATA I/O	Mode	I_{DD}
H	X	X	—	Hi-Z	Standby	I_{DDs} , I_{DDs1}
L	X	L	Stable	D_{IN}	Write	I_{DDA} , I_{DDA1}
L	L	H	Stable	D_{OUT}	Read	I_{DDA} , I_{DDA1}
L	H	H	Stable	Hi-Z	Output disable	I_{DDA} , I_{DDA1}

X : "H" or "L", — : "H", "L" or "Hi-Z"

● Read Mode

The data appear when the address is set while holding $\overline{CS} = "L"$, $\overline{OE} = "L"$ and $\overline{WE} = "H"$. When $\overline{OE} = "L"$, DATA I/O terminals are in high impedance state, that makes circuit design and bus control easy.

● Write Mode

There are the following 3 ways of writing data into memory.

- (1) Hold $\overline{CS} = "L"$ and $\overline{WE} = "L"$, set address
- (2) Hold $\overline{CS} = "L"$ then set address and give "L" pulse to $\overline{WE}$.
- (3) After setting addresses, give "L" pulse to both $\overline{CS}$ and $\overline{WE}$.

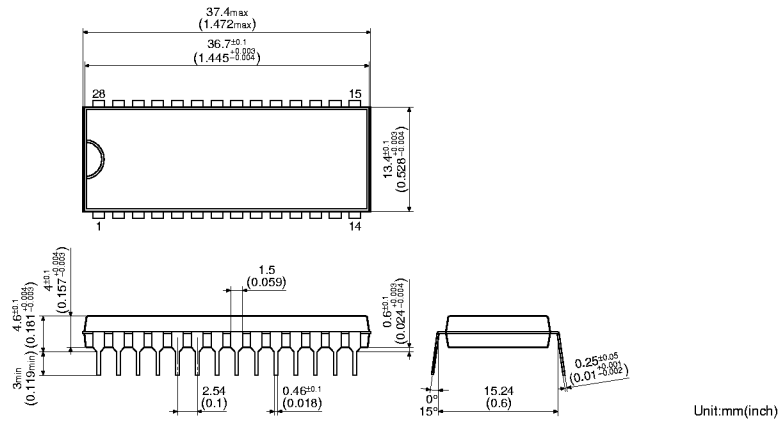
In above any case data on the DATA I/O terminals are latched up into the chip when $\overline{CS}$ or $\overline{WE}$ is in positive-going. Since DATA I/O terminals are high impedance when $\overline{CS}$ or $\overline{OE} = "H"$, bus contention between data driver and memory outputs can be avoided.

● Standby Mode

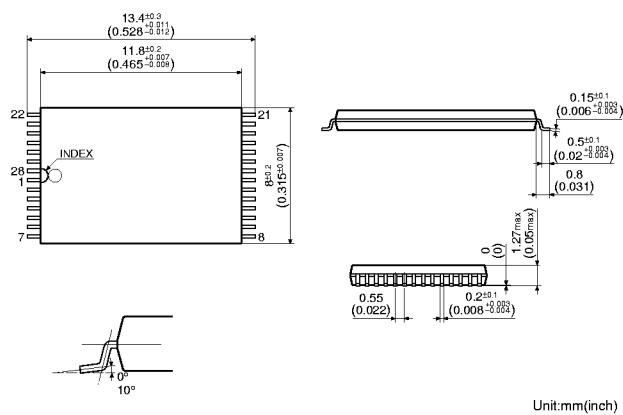
When $\overline{CS}$ is "H" the chip become in the standby mode. In this mode, DATA I/O terminals are high impedance and all inputs of addresses, $\overline{WE}$ and data can be any "H" or "L". When $\overline{CS}$ is over than $V_{DD}-0.2V$, the chip is in the data retention battery backup mode, in this case, there is a small current in the chip which flow through the high resistances of the memory cells.

■ PACKAGE DIMENSIONS

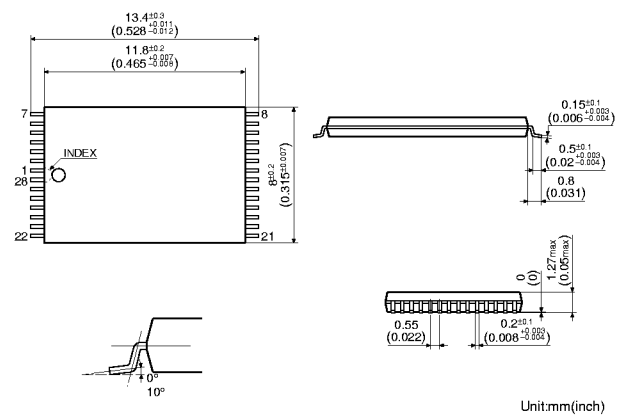
Plastic DIP-28 pin (600mil)



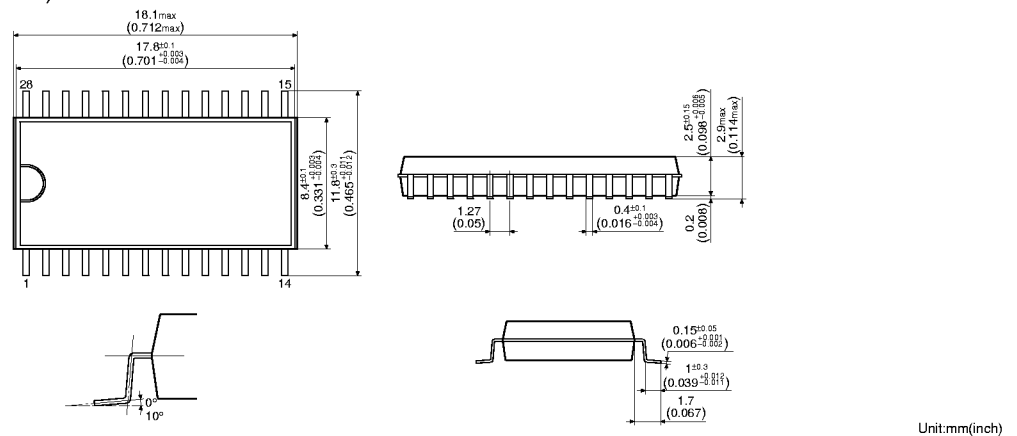
Plastic TSOP(I) - 28 pin



Plastic TSOP(I) - 28 pin -R1



Plastic SOP2-28 pin (450mil)



CHARACTERISTICS CURVES

